

Silicon NPN Power Transistors

2N5293 2N5295 2N5297

DESCRIPTION

- With TO-220 package
- High power dissipation

APPLICATIONS

- Power amplifier and medium speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

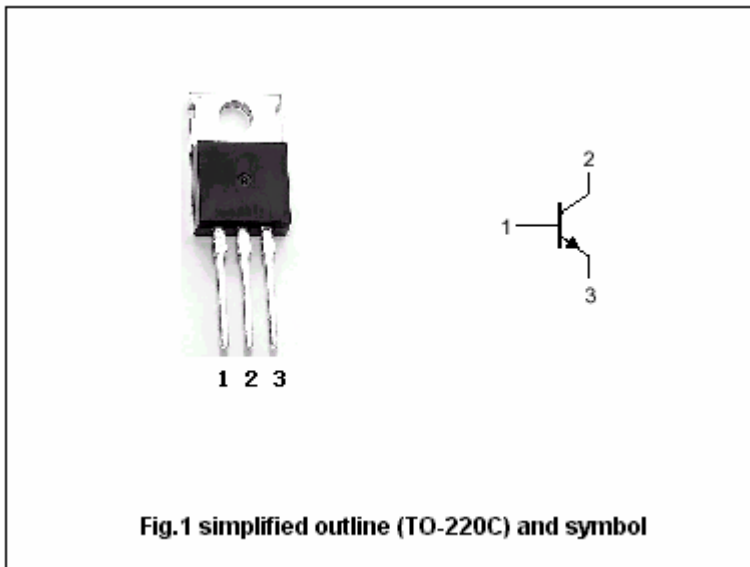


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5293	80	V
		2N5295	60	
		2N5297	80	
V _{CEO}	Collector-emitter voltage	2N5293	70	V
		2N5295	40	
		2N5297	60	
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		4	A
I _B	Base current		2	A
P _T	Total power dissipation	T _C =25	36	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	3.47	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N5293	I _C =0.1A ; I _B =0	70		V
		2N5295		40		
		2N5297		60		
V _{CEsat}	Collector-emitter saturation voltage	2N5293	I _C =0.5A; I _B =0.05A		1.0	V
		2N5295	I _C =1.0A; I _B =0.1A			
		2N5297	I _C =1.5A; I _B =0.15A			
V _{BE}	Base-emitter on voltage	2N5293	I _C =0.5A ; V _{CE} =4V		1.1	V
		2N5295	I _C =1.0A ; V _{CE} =4V		1.3	
		2N5297	I _C =1.5A ; V _{CE} =4V		1.5	
I _{CEV}	Collector cut-off current	2N5293/5297	V _{CE} =65V; V _{BE} =1.5V T _C =150		0.5 3.0	mA
		2N5295	V _{CE} =35V; V _{BE} =1.5V T _C =150		2.0 5.0	
I _{CER}	Collector cut-off current	2N5293/5297	V _{CE} =50V; R _{BE} =100 T _C =150		0.5 2.0	mA
I _{EBO}	Emitter cut-off current	2N5295	V _{EB} =7V; I _C =0		1.0	mA
		2N5293/5297	V _{EB} =5V; I _C =0			
h _{FE}	DC current gain	2N5293	I _C =0.5A ; V _{CE} =4V	30	120	
		2N5295	I _C =1.0A ; V _{CE} =4V			
		2N5297	I _C =1.5A ; V _{CE} =4V	20	80	
f _T	Transition frequency		I _C =0.2A ; V _{CE} =4V	0.8		MHz
t _{on}	Turn-on time	2N5293	I _C =0.5A; I _B =0.05A; V _{CC} =30V		5.0	μs
		2N5295	I _C =1.0A; I _B =0.1A; V _{CC} =30V			
		2N5297	I _C =1.5A; I _B =0.15A; V _{CC} =30V			
t _{off}	Turn-off time	2N5293	I _C =0.5A; I _B =0.05A; V _{CC} =30V		15	μs
		2N5295	I _C =1.0A; I _B =0.1A; V _{CC} =30V			
		2N5297	I _C =1.5A; I _B =0.15A; V _{CC} =30V			

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)